

# **CD40147BMS**

December 1992

# 10 Line to 4 Line BCD Priority Encoder

#### **Features**

- High Voltage Type (20V Rating)
- Encodes 10 Line to 4 Line BCD
- · Active Low Inputs and Outputs
- 100% Tested for Quiescent Current at 20V
- 5V, 10V and 15V Parametric Ratings
- Maximum Input Current of 1μA at 18V Over Full Package Temperature Range; 100nA at 18V and +25°C
- Noise Margin (Over Full Package/Temperature Range)
  - 1V at VDD = 5V
  - 2V at VDD = 10V
  - 2.5V at VDD = 15V
- Standardized Symmetrical Output Characteristics
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"

## **Applications**

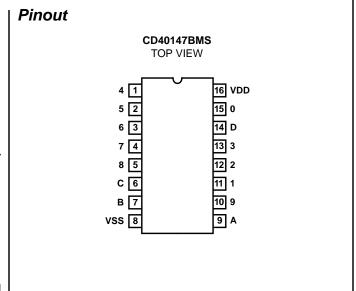
- · Keyboard Encoding
- 10 Line to BCD Encoding
- Range Selection

#### Description

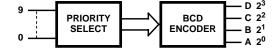
CD40147BMS CMOS encoder features priority encoding of the inputs to ensure that only the highest order data line is encoded. Ten data input lines (0-9) are encoded to four line (8, 4, 2, 1) BCD. The highest priority line is line 9. All four output lines are logic 1 (VSS) when all input lines are logic 0. All inputs and outputs are buffered, and each output can drive one TTL low power Schottky load. The CD40147BMS is functionally similar to the TTL 54/74147 if pin 15 is tied low.

The CD40147BMS is supplied in these 16-lead outline packages:

Braze Seal DIP H4T Frit Seal DIP H1E Ceramic Flatpack H6W



## Functional Diagram



#### **Absolute Maximum Ratings**

#### DC Supply Voltage Range, (VDD) . . . . . -0.5V to +20V (Voltage Referenced to VSS Terminals) Input Voltage Range, All Inputs . . . . . . . -0.5V to VDD +0.5V DC Input Current, Any One Input ......±10mA Operating Temperature Range . . . . . . . . -55°C to +125°C Package Types D, F, K, H Storage Temperature Range (TSTG) . . . . . . . -65°C to +150°C Lead Temperature (During Soldering) . . . . . . . . . +265°C At Distance $1/16 \pm 1/32$ Inch (1.59mm $\pm$ 0.79mm) from case for 10s Maximum

#### **Reliability Information**

Thermal Resistance	$\theta_{ja}$	θ <sub>jc</sub> 20°C/W
Ceramic DIP and FRIT Package	80°C/W	20°C/W
Flatpack Package	70°C/W	20°C/W
Maximum Package Power Dissipation (PD		
For $T_A = -55^{\circ}C$ to $+100^{\circ}C$ (Package Typ		
For $T_A = +100^{\circ}$ C to $+125^{\circ}$ C (Package T		
Lineari	ty at 12mW/	C to 200mW
Device Dissipation per Output Transistor .		100mW
For T <sub>A</sub> = Full Package Temperature Ran	ige (All Pack	age Types)
Junction Temperature		+175°C

#### TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

				GROUP A		LIN	IITS	
PARAMETER	SYMBOL	CONDITIONS (	NOTE 1)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND  VDD = 18V, VIN = VDD or GND		1	+25°C	-	2	μΑ
				2	+125°C	-	200	μА
				3	-55°C	-	2	μА
Input Leakage Current	eakage Current IIL VIN = VDD or GN		VDD = 20	1	+25°C	-100	-	nA
				2	+125°C	-1000	-	nA
			VDD = 18V	3	-55°C	-100	-	nA
Input Leakage Current	IIH	VIN = VDD or GND	VDD = 20	1	+25°C	-	100	nA
				2	+125°C	-	1000	nA
			VDD = 18V	3	-55°C	-	100	nA
Output Voltage	VOL15	VDD = 15V, No Load		1, 2, 3	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH15	VDD = 15V, No Load (Note 3)		1, 2, 3	+25°C, +125°C, -55°C	14.95	-	V
Output Current (Sink)	IOL5	VDD = 5V, VOUT = 0.	4V	1	+25°C	0.53	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0	0.5V	1	+25°C	1.4	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1	1.5V	1	+25°C	3.5	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V		1	+25°C	-	-0.53	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.	.5V	1	+25°C	-	-1.8	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9	9.5V	1	+25°C	-	-1.4	mA
Output Current (Source)	IOH15	VDD = 15V, VOUT = 1	13.5V	1	+25°C	-	-3.5	mA
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10	μΑ	1	+25°C	-2.8	-0.7	V
P Threshold Voltage	VPTH	VSS = 0V, IDD = 10μ/	4	1	+25°C	0.7	2.8	V
Functional	F	VDD = 2.8V, VIN = VE	DD or GND	7	+25°C	VOH>	VOL <	V
		VDD = 20V, VIN = VD	D or GND	7	+25°C	VDD/2	VDD/2	
		VDD = 18V, VIN = VD	D or GND	8A	+125°C			
		VDD = 3V, VIN = VDD	or GND	8B	-55°C			
Input Voltage Low (Note 2)	VIL	VDD = 5V, VOH > 4.5	V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	-	1.5	V
Input Voltage High (Note 2)	VIH	VDD = 5V, VOH > 4.5	V, VOL < 0.5V	1, 2, 3	+25°C, +125°C, -55°C	3.5	-	V
Input Voltage Low (Note 2)	VIL	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	-	4	V
Input Voltage High (Note 2)	VIH	VDD = 15V, VOH > 13 VOL < 1.5V	3.5V,	1, 2, 3	+25°C, +125°C, -55°C	11	-	V

NOTES: 1. All voltages referenced to device GND, 100% testing being 3. For accuracy, voltage is measured differentially to VDD. Limit

2. Go/No Go test with limits applied to inputs.

implemented. is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

			GROUP A		LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS (NOTE 1, 2)	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL1	VDD = 5V, VIN = VDD or GND	9	+25°C	-	900	ns
In Phase Output	TPLH1		10, 11 +125°C,			1215	ns
Transition Time	TTHL	VDD = 5V, VIN = VDD or GND	9	+25°C	-	200	ns
	TTLH		10, 11	+125°C, -55°C	i	270	ns

#### NOTES:

- 1. CL = 50pF, RL = 200K, Input TR, TF < 20ns.
- 2.  $-55^{\circ}$ C and  $+125^{\circ}$ C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIN	LIMITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 5V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	1	μΑ
				+125°C	-	30	μА
		VDD = 10V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μА
				+125°C	-	60	μА
		VDD = 15V, VIN = VDD or GND	1, 2	-55°C, +25°C	-	2	μА
				+125°C	-	120	μА
Output Voltage	VOL	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOL	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	-	50	mV
Output Voltage	VOH	VDD = 5V, No Load	1, 2	+25°C, +125°C, -55°C	4.95	-	V
Output Voltage	VOH	VDD = 10V, No Load	1, 2	+25°C, +125°C, -55°C	9.95	-	V
Output Current (Sink)	Current (Sink) IOL5 VDD = 5V, VOUT = 0.4V 1, 2 +125°C 0.3	0.36	-	mA			
				-55°C	0.64	-	mA
Output Current (Sink)	IOL10	VDD = 10V, VOUT = 0.5V	1, 2	+125°C	0.9	-	mA
				-55°C	1.6	-	mA
Output Current (Sink)	IOL15	VDD = 15V, VOUT = 1.5V	1, 2	+125°C	2.4	-	mA
				-55°C	4.2	-	mA
Output Current (Source)	IOH5A	VDD = 5V, VOUT = 4.6V	1, 2	+125°C	-	-0.36	mA
				-55°C	-	-0.64	mA
Output Current (Source)	IOH5B	VDD = 5V, VOUT = 2.5V	1, 2	+125°C	-	-1.15	mA
				-55°C	-	-2.0	mA
Output Current (Source)	IOH10	VDD = 10V, VOUT = 9.5V	1, 2	+125°C	-	-0.9	mA
				-55°C	-	-1.6	mA
Output Current (Source)	IOH15	VDD =15V, VOUT = 13.5V	1, 2	+125°C	-	-2.4	mA
				-55°C	-	-4.2	mA
Input Voltage Low	VIL	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	-	3	V
Input Voltage High	VIH	VDD = 10V, VOH > 9V, VOL < 1V	1, 2	+25°C, +125°C, -55°C	+7	-	V

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

					LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Propagation Delay	TPHL	VDD = 10V	1, 2, 3	+25°C	-	400	ns
In Phase Output	TPLH	VDD = 15V	1, 2, 3	+25°C	-	300	ns
Propagation Delay	TPHL	VDD = 5V	1, 2, 3	+25°C	-	850	ns
Out of Phase Output	TPLH	VDD = 10V	1, 2, 3	+25°C	-	350	ns
		VDD = 15V	1, 2, 3	+25°C	-	250	ns
Transition Time	TTLH	VDD = 10V	1, 2, 3	+25°C	-	100	ns
		VDD = 15V	1, 2, 3	+25°C	-	80	ns
Input Capacitance	CIN	Any Input	1, 2	+25°C	-	7.5	pF

#### NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

					LIM	IITS	
PARAMETER	SYMBOL	CONDITIONS	NOTES	TEMPERATURE	MIN	MAX	UNITS
Supply Current	IDD	VDD = 20V, VIN = VDD or GND	1, 4	+25°C	-	7.5	μΑ
N Threshold Voltage	VNTH	VDD = 10V, ISS = -10μA	1, 4	+25°C	-2.8	-0.2	V
N Threshold Voltage Delta	ΔVTN	VDD = 10V, ISS = -10μA	1, 4	+25°C	-	±1	V
P Threshold Voltage	VTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	0.2	2.8	V
P Threshold Voltage Delta	ΔVTP	VSS = 0V, IDD = 10μA	1, 4	+25°C	-	±1	V
Functional	F	VDD = 18V, VIN = VDD or GND	1	+25°C	VOH >	VOL <	V
		VDD = 3V, VIN = VDD or GND			VDD/2	VDD/2	
Propagation Delay Time	TPHL TPLH	VDD = 5V	1, 2, 3, 4	+25°C	-	1.35 x +25°C Limit	ns

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS +25°C

PARAMETER	SYMBOL	DELTA LIMIT
Supply Current - MSI-1	IDD	± 0.2μA
Output Current (Sink)	IOL5	± 20% x Pre-Test Reading
Output Current (Source)	IOH5A	± 20% x Pre-Test Reading

**TABLE 6. APPLICABLE SUBGROUPS** 

CONFORMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD
Initial Test (Pre Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 1 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A
Interim Test 2 (Post Burn-In)	100% 5004	1, 7, 9	IDD, IOL5, IOH5A

#### TABLE 6. APPLICABLE SUBGROUPS (Continued)

CONFO	RMANCE GROUP	MIL-STD-883 METHOD	GROUP A SUBGROUPS	READ AND RECORD		
PDA (Note	e 1)	100% 5004	1, 7, 9, Deltas			
Interim Test	est 3 (Post Burn-In) 100% 5004 1, 7, 9		IDD, IOL5, IOH5A			
PDA (Note 1)		100% 5004	5004 1, 7, 9, Deltas			
Final Test		100% 5004	2, 3, 8A, 8B, 10, 11			
Group A		Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11			
Group B	Subgroup B-5	Sample 5005	1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas	Subgroups 1, 2, 3, 9, 10, 11		
	Subgroup B-6	Sample 5005	1, 7, 9			
Group D		oup D Sample 5005		Subgroups 1, 2 3		

NOTE: 1.5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

#### **TABLE 7. TOTAL DOSE IRRADIATION**

	MIL-STD-883	TE	ST	READ AND RECORD		
CONFORMANCE GROUPS	METHOD	PRE-IRRAD	POST-IRRAD	PRE-IRRAD	POST-IRRAD	
Group E Subgroup 2	5005	1, 7, 9	Table 4	1, 9	Table 4	

#### TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

					OSCIL	LATOR
FUNCTION	OPEN	GROUND	VDD	9V ± -0.5V	50kHz	25kHz
Static Burn-In 1 Note 1	6, 7, 9, 14	1-5, 8, 10-13, 15	16			
Static Burn-In 2 Note 1	6, 7, 9, 14	8	1-5, 10-13, 15, 16			
Dynamic Burn- In Note 1	-	8	16	6, 7, 9, 14	1, 3, 11, 13	2, 4, 5, 10, 12, 15
Irradiation Note 2	6, 7, 9, 14	8	1-5, 10-13, 15, 16			

#### NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K  $\pm$  5%, VDD = 18V  $\pm$  0.5V
- 2. Each pin except VDD and GND will have a series resistor of 47K  $\pm$  5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD =  $10V \pm 0.5V$

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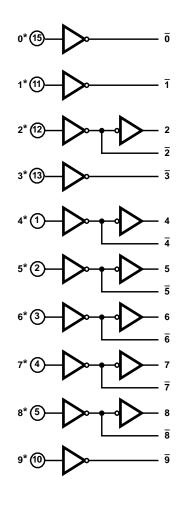
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# Logic Diagram



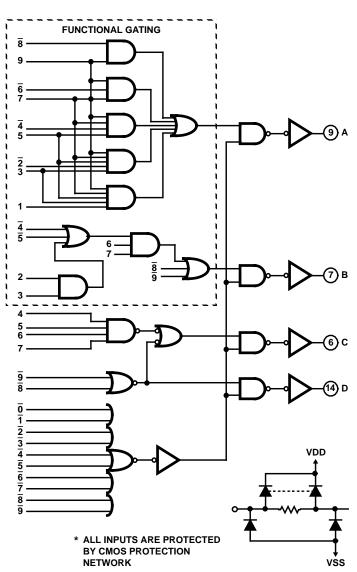


FIGURE 1.

## **TRUTH TABLE (Negative Logic)**

				INP	UTS						OUTI	PUTS	
0	1	2	3	4	5	6	7	8	9	D	С	В	Α
0	0	0	0	0	0	0	0	0	0	1	1	1	1
1	0	0	0	0	0	0	0	0	0	0	0	0	0
X	1	0	0	0	0	0	0	0	0	0	0	0	1
X	Х	1	0	0	0	0	0	0	0	0	0	1	0
X	Х	Χ	1	0	0	0	0	0	0	0	0	1	1
Х	Х	Χ	Х	1	0	0	0	0	0	0	1	0	0
X	Х	Χ	Х	Х	1	0	0	0	0	0	1	0	1
X	Х	Χ	Х	Χ	Χ	1	0	0	0	0	1	1	0
X	Х	Χ	Х	Χ	Χ	Χ	1	0	0	0	1	1	1
Х	Х	Х	Х	Χ	Χ	Х	Х	1	0	1	0	0	0
Х	Х	Х	Х	Х	Х	Х	Х	Х	1	1	0	0	1

 $0 = \text{High level} \quad 1 = \text{Low level} \quad X = \text{Don't care}$ 

# Typical Performance Characteristics

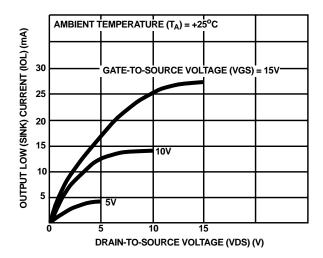


FIGURE 2. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

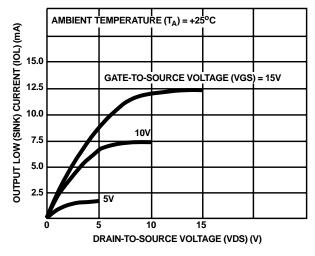


FIGURE 3. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

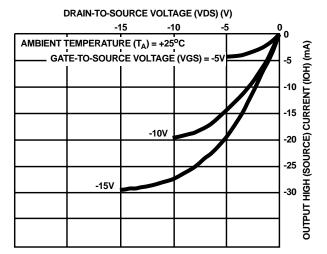


FIGURE 4. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

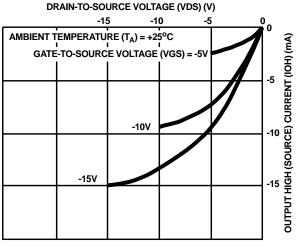


FIGURE 5. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

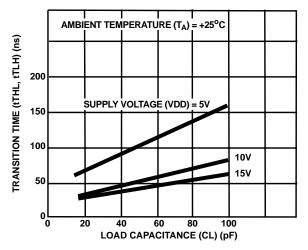


FIGURE 6. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

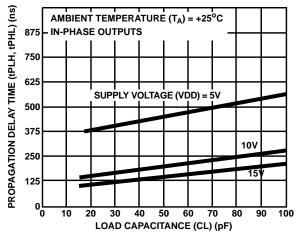


FIGURE 7. PROPAGATION DELAY TIME AS A FUNCTION OF LOAD CAPACITANCE

# Typical Performance Characteristics (Continued)

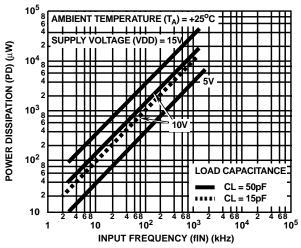
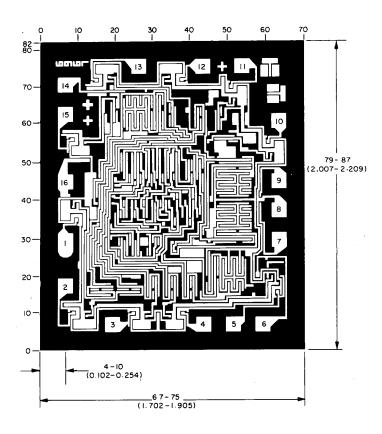


FIGURE 8. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT FREQUENCY

## Chip Dimensions and Pad Layout



Dimensions in parenthesis are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).

**METALLIZATION:** Thickness: 11kÅ – 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

**BOND PADS:** 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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